

IMPACT OF IC TECHNOLOGY ON THE POWER PROCESSING INDUSTRY



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PSMA Perspective - 5 Year Roadmap



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What drives the PSMA requirements and how do we satisfy them?

How is IC technology evolving?

What will this progress mean to the power industry?

How IC technology itself provides solutions to the problems we face.

Examples of how IC technologies are enablers for power solutions.



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From Intel Technology Symposium September 2003

IC technology progress will enable Intel to build processors with more than a billion transistors, running at about 20 GHz by 2010.



As Gate lengths continue to shrink, Gate leakage becomes excessive. SiO₂ limit ~ 23 Angstroms

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- Using higher K dielectrics (SiO₂ = 4.5) required for thicker gate Tox
- Short channel lengths require shallower SD junctions. Higher doping required to maintain low resistance.
- Limits approached as devices approach atomic dimensions.







BY 2008, Vcc will fall from 1.3 to 0.8 volts and lcc will rise to 150 amps.

Load slew rates will dictate higher controller bandwidth & lower Zout

Desktop CPU Current Trend



60 Amp Transient Load Step



Three phase controller solution

from Fred Lee's "High frequency solutions for 12 volt VR" CPES September, 2003

MB for Pentium IV uP

New circuit techniques required as part of future solutions

Power Industry Challenges

- Increased current requirements at ever lower voltages New power devices required
- Increased load transients caused by faster switching components.

Faster power switching required

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Current circuit approaches untenable due space constraints

New more space efficient circuit topology required.

Power solutions from this technology

Shorter channel lengths lead to:

Improved R_{DS(on)} cm² Improved cells per cm²

Single and dual Resurf from improved process control drive:

Higher voltage, higher cell density power devices

Copper metallization

Lower thermal resistance Lower parasitic resistance

Leadless packaging Improved thermal resistance

Projected Power MOS Cell Density

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50% packing density improvement from strip to cell topology

Cell Density (MCells / in2)

DMOS Structure

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Trench solves JFET issueproves higher cell density

Existing Technology *Multiple Epi layers Multiple P implants*

Future Technology

Trench generated P regions and single Epi layer to provide die size improvement

P Regions shape space charge widening and allows device to be smaller

Drain

Year

N

Packaging Technology...

Fully integrated IC and Power delivery System

High Power Notebook Adapter with PFC

Today's mainstream power solutions are dominated by "ugly" passives (cost driven)
Challenge for semiconductor vendors is to reduce the passive real estate with "smarter" semiconductor solution kits – need optimum partitioning, advanced technologies

Power Trends Summary

 Insatiable demand for increased power density will drive innovative power designs to deliver
 higher efficiency solutions.

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>low inductance thermally superior packaging.

Higher frequency solutions will require higher levels of integration in lower inductance packages.

